

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L20	132	((gate adj (insulating or dielectric or oxide)) near2 (on or over or top or overlying) near2 (semiconductor adj layer)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:48
L21	6	((gate adj (insulating or dielectric or oxide)) near2 (on or over or top or overlying) near2 (semiconductor adj layer)) with (tft or (thin adj film adj transistor))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:50
L22	12	((gate adj (insulating or dielectric or oxide)) near3 (on or over or top or overlying) near3 (semiconductor adj layer)) with (tft or (thin adj film adj transistor))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 13:50
L23	5	I11 and ((gate adj (insulating or dielectric or oxide)) near5 (semiconductor adj layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 15:09
L24	4	I11 and ((gate adj (insulating or dielectric or oxide)) near5 (semiconductor adj layer)) and (ldd or (lightly adj doped) or (low adj impurity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 15:10
L25	4	I11 and ((gate adj (insulating or dielectric or oxide)) near5 (semiconductor adj layer)) and (ldd or (lightly adj doped) or (low adj density adj impurity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 15:11
L26	1092	((gate adj (insulating or dielectric or oxide)) near5 (semiconductor adj layer)) and (ldd or (lightly adj doped) or (low adj density adj impurity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 15:11
L27	419	((gate adj (insulating or dielectric or oxide)) near5 (semiconductor adj layer)).clm. and (ldd or (lightly adj doped) or (low adj density adj impurity))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 15:11
L28	105	((gate adj (insulating or dielectric or oxide)) near5 (semiconductor adj layer)).clm. and (ldd or (lightly adj doped) or (low adj density adj impurity)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 15:39

L29	14	((gate adj (insulating or dielectric or oxide)) near5 (semiconductor adj layer)).clm. same (ldd or (lightly adj doped) or (low adj density adj impurity)).clm. same (tft or (thin adj film adj transistor)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 16:14
L30	2	((gate adj (insulating or dielectric or oxide)) near5 (semiconductor adj layer)).clm. same (ldd or (lightly adj doped) or (low adj density adj impurity)).clm. same (tft or (thin adj film adj transistor)).clm. and ((gate adj (insulating or dielectric or oxide)) near5 (on or over or overlying)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 16:16
L31	3	((gate adj (insulating or dielectric or oxide)) near5 (semiconductor adj layer)).clm. same (ldd or (lightly adj doped) or (low adj density adj impurity)).clm. same (tft or (thin adj film adj transistor)).clm. and ((gate adj (insulating or dielectric or oxide)) near5 (on or over or overlying))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 16:17
L32	10	((gate adj (insulating or dielectric or oxide)) near5 (semiconductor adj layer)).clm. same (ldd or (lightly adj doped) or (low adj density adj impurity)).clm. same (tft or (thin adj film adj transistor)).clm. and ((gate adj (insulating or dielectric or oxide)) near5 (form or forming or formed)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 16:18
L33	0	((gate adj (insulating or dielectric or oxide)) near5 (semiconductor adj layer)).clm. same (ldd or (lightly adj doped) or (low adj density adj impurity)).clm. same (tft or (thin adj film adj transistor)).clm. and ((gate adj (insulating or dielectric or oxide)) near5 (form or forming or formed) near5 (on or over or overlying) near5 (semiconductor adj layer)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 16:18

L34	0	((gate adj (insulating or dielectric or oxide)) near5 (semiconductor adj layer)).clm. same (ldd or (lightly adj doped) or (low adj density adj impurity)).clm. same (tft or (thin adj film adj transistor)).clm. and ((gate adj (insulating or dielectric or oxide)) near5 (form or forming or formed) near10 (on or over or overlying) near10 (semiconductor adj layer)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/07 16:18
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